



东莞市华远电子有限公司

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TO-92 Plastic-Encapsulate Transistors

2SC2216 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 300m W ($T_{amb}=25$)

Collector current

I_{CM} : 50mA

Collector-base voltage

$V_{(BR)CBO}$: 50V

Operating and storage junction temperature range

T_J , T_{stg} : -55 to +150

TO-92



1.BASE

2.EMITTER

3.COLLECTOR

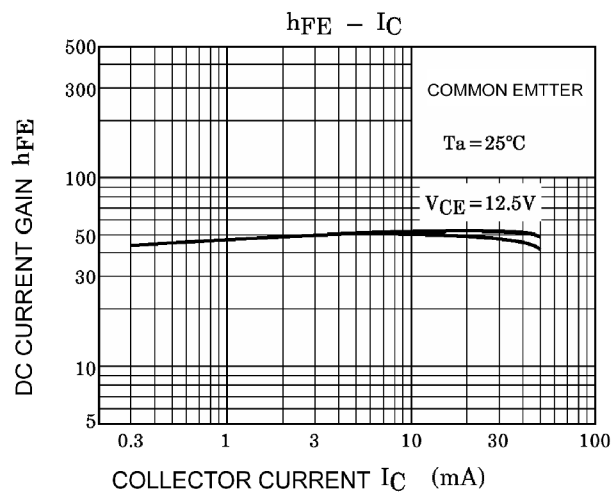
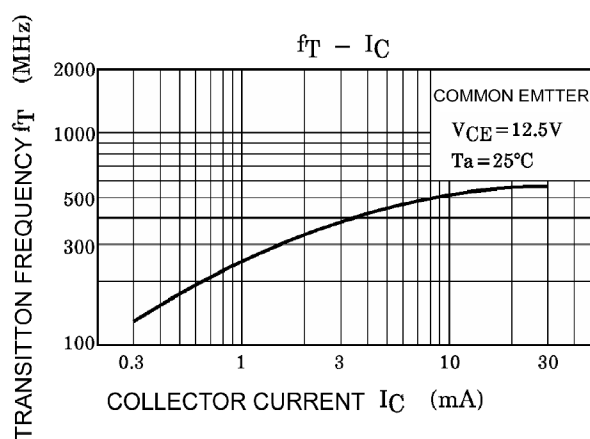
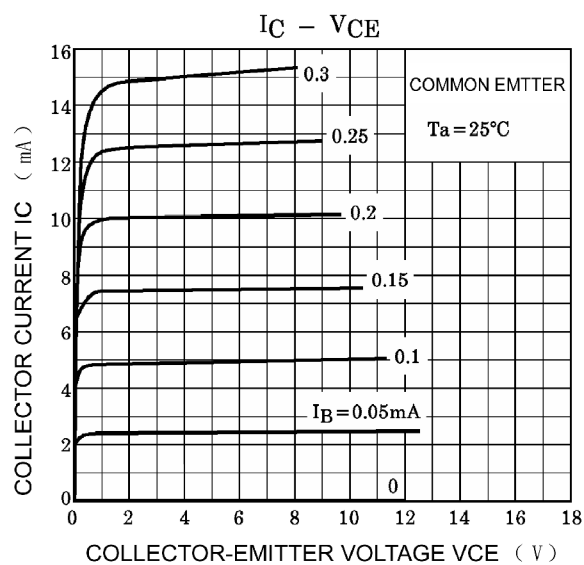
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ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

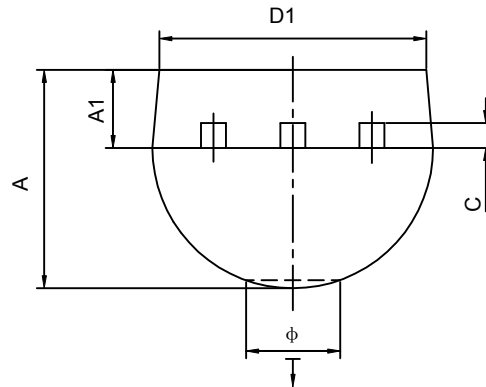
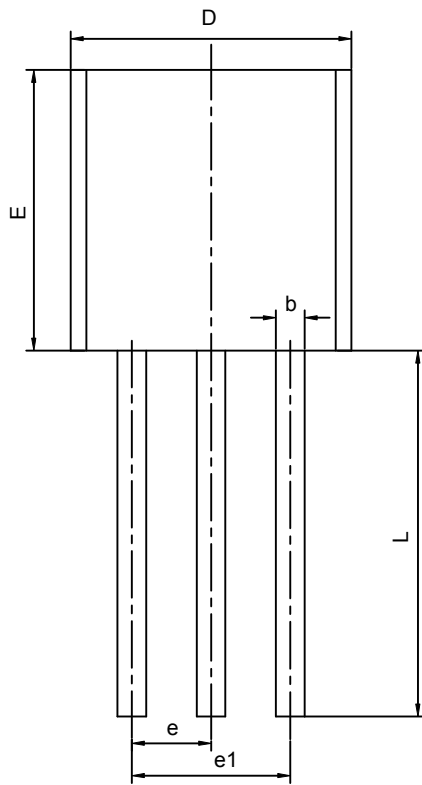
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A$, $I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA$, $I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A$, $I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=12.5V$, $I_C=12.5mA$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15mA$, $I_B=1.5mA$			0.2	V
Bass-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15mA$, $I_B=1.5mA$			1.5	V
Transition frequency	f_T	$V_{CE}=12.5V$, $I_C=12.5mA$ $f=100MHz$	300			MHz

Typical Characteristics

2SC2216



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
\downarrow	0.000	0.380	0.000	0.015